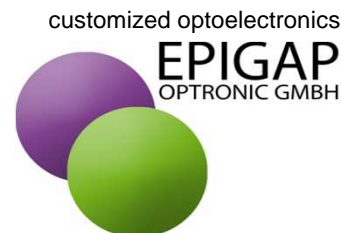


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Product Data Sheet

LED Chip Infra Red

EOLC-770-11

Rev. 01 aus 2011

Radiation	Type	Electrodes
Infra red	DDH	P (anode) up

Dimensions

Typ. Thickness: 165 (±55) μm
 anode: gold alloy, 1.5 μm
 Cathode: gold alloy, 0.5 μm, structured, 25% covered

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20mA	V _F		1.5		V
Forward voltage	I _F =350mA	V _F		1.8		V
Reverse voltage	I _R =100μA	V _R	5			V
Radiant power*	I _F =20mA	Φ _e	2.5	3.5		mW
Radiant power*	I _F =350mA	Φ _e		70		mW
Peak wavelength	I _F =350mA	λ _p	750	765	780	nm
Spectral bandwidth at 50%	I _F =350mA	Δλ _{0.5}		30		nm
Switching time	I _F =20mA	t _r , t _f		15		ns

*Measured on bare chip on TO18 header

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Qty.
EOLC-770-11				

Packing

Chips on adhesive film with wire bond side up